



SMP30-xxx

TELECOM EQUIPMENT PROTECTION: TRISIL™

FEATURES

- Bidirectional crowbar protection
- Voltage range from 62V to 270V
- Low capacitance from 12pF to 20pF typ. @ 50V
- Low leakage current: $I_R = 2\mu\text{A}$ max.
- Holding current: $I_H = 150$ mA min.
- Repetitive peak pulse current:
 $I_{PP} = 30$ A (10/1000 μs)

MAIN APPLICATIONS

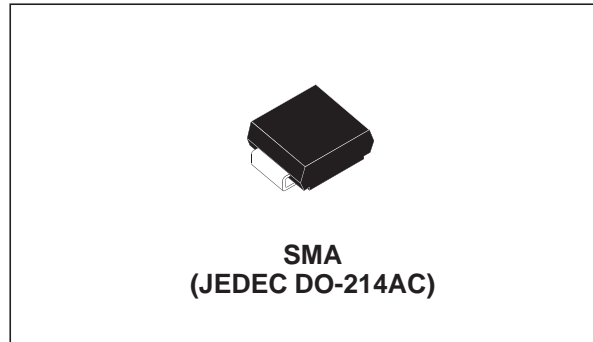
Telecommunication equipment such as

- Analog and digital line cards (xDSL, T1/E1, ISDN...).
- Terminals (phone, fax, modem...) and central office equipment.

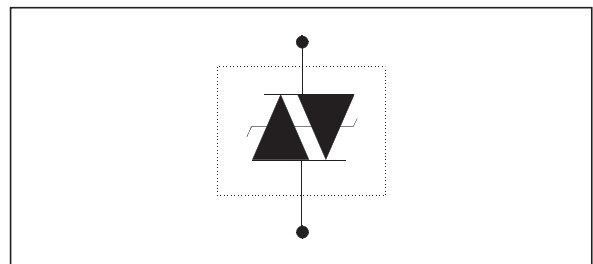
DESCRIPTION

The SMP30-xxx series has been designed to protect telecommunication equipment against lightning and transient induced by AC power lines.

The package / die size ratio has been optimized by using the SMA package.



SCHEMATIC DIAGRAM



BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. Trisils are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part 68. Trisils have UL94 V0 resin approved. SMA package is JEDEC registered. (Trisils are UL 497B approved - file: E136224).

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IN COMPLIANCES WITH THE FOLLOWING STANDARDS

Standard	Peak Surge Voltage (V)	Voltage Waveform (μ s)	Required peak current (A)	Current Waveform (μ s)	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500	2/10	500	2/10	20
	1000	10/1000	100	10/1000	24
GR-1089 Core Second level	5000	2/10	500	2/10	40
GR-1089 Core Intra-building	1500	2/10	100	2/10	0
ITU-T-K20 / K21	6000 1500	10/700	150 37.5	5/310	110 0
ITU-T-K20 (IEC61000-4-2)	6000 8000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000	10/700	100	5/310	60
	2000		50		10
VDE0878	4000	1.2/50	100	1/20	18
	2000		50		0
IEC61000-4-5	4000	10/700	100	5/310	60
	4000	1.2/50	100	8/20	18
FCC Part 68, lightning surge type A	1500	10/160	200	10/160	26
	800	10/560	100	10/560	15
FCC Part 68, lightning surge type B	1000	9/720	25	5/320	0

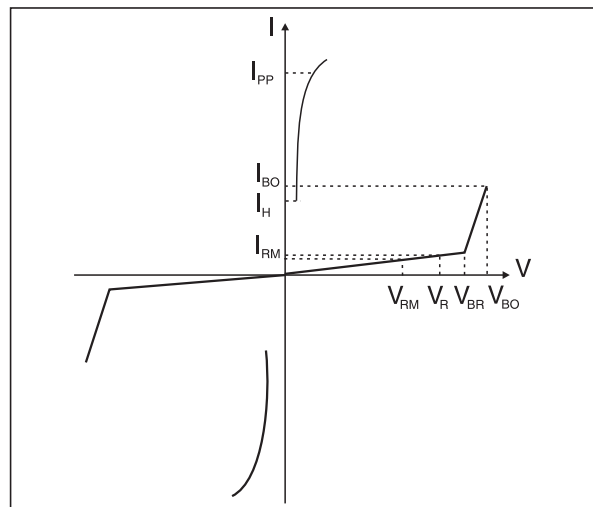
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient with recommended footprint	120	$^{\circ}C/W$
$R_{th(j-l)}$	Junction to leads	30	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS

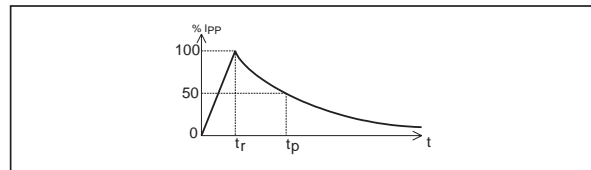
($T_{amb} = 25^{\circ}C$)

Symbol	Parameter
V_{RM}	Stand-off voltage
I_{RM}	Leakage current at V_{RM}
V_R	Continuous reverse voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_H	Holding current
I_{BO}	Breakover current
I_{PP}	Peak pulse current
C	Capacitance



ABSOLUTE RATINGS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit	
I_{PP}	Repetitive peak pulse current:	10/1000 μs	30	A
		8/20 μs	70	
		10/560 μs	35	
		5/310 μs	40	
		10/160 μs	45	
		1/20 μs	70	
		2/10 μs	100	
I_{FS}	Fail safe mode: maximum current	8/20 μs	2.5	kA
I_{TSM}	Non repetitive surge peak on-state current (Sinusoidal)	t = 20ms	15	A
		t = 16.6ms	17	
		t = 0.2s	8.5	
		t = 2s	4.5	
I^2t	I^2t value for fusing	t = 16.6ms	2.1	A^2s
		t = 20ms	2.25	
T_L	Maximum lead temperature for soldering during 10 s.	260	$^{\circ}\text{C}$	
T_{stg} T_j	Storage temperature range	- 55 to + 150	$^{\circ}\text{C}$	
	Maximum junction temperature	150	$^{\circ}\text{C}$	

Repetitive peak pulse currenttr: rise time (μs)tp: pulse duration time (μs)ex: Pulse waveform 10/1000 μs tr = 10 μs tp = 1000 μs 

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ELECTRICAL PARAMETERS (Tamb = 25°C)

Type	I _{RM} @ V _{RM} max		I _R @ V _R MAX		DYNAMIC V _{BO} @ I _{BO} max		STATIC V _{BO} @ I _{BO} max		I _H min	C typ.	C typ.
	μA	V	μA	V	V	mA	V	mA	mA	pF	pF
SMP30-62	2	56	50	62	85	800	82	800	150	20	40
SMP30-68		61		68	93		90		150	20	40
SMP30-100		90		100	135		133		150	16	35
SMP30-120		108		120	160		160		150	16	30
SMP30-130		117		130	173		173		150	14	30
SMP30-180		162		180	235		240		150	14	25
SMP30-200		180		200	262		267		150	12	25
SMP30-220		198		220	285		293		150	12	25
SMP30-240		216		240	300		320		150	12	25
SMP30-270		243		270	350		360		150	12	25

Note 1: I_R measured at V_R guarantee V_{BRmin} ≥ V_R

Note 2: See functional breakover voltage test circuit 1.

Note 3: See test circuit 2.

Note 4: See functional holding current test circuit 3.

Note 5: V_R = 50V bias, V_{RMS} = 1V, F = 1MHz.

Note 6: V_R = 2V bias, V_{RMS} = 1V, F = 1MHz

Fig. 1: Non repetitive surge peak on-state current versus overload duration (T_j initial = 25°C)

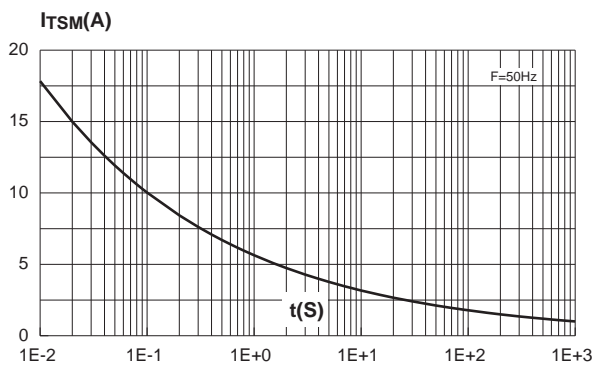


Fig. 2: On-state voltage versus on-state current (typical values).

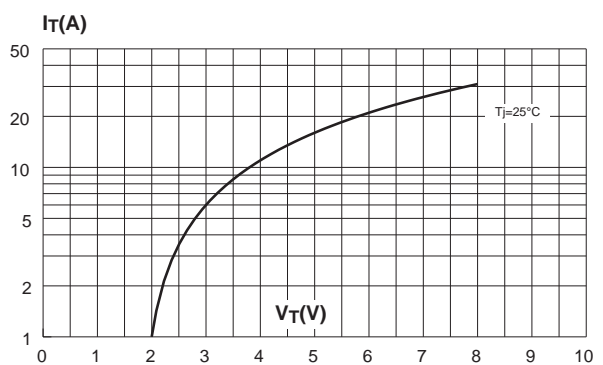


Fig. 3: Relative variation of holding current versus junction temperature.

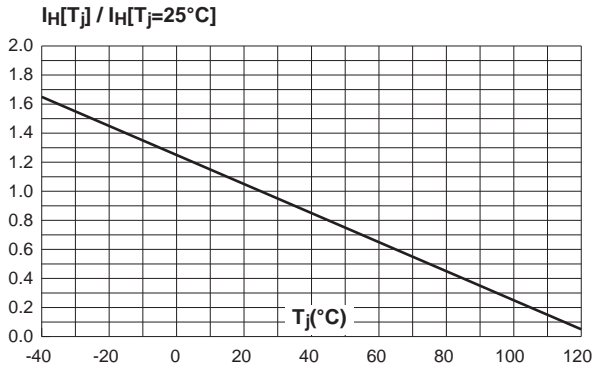


Fig. 4: Relative variation of breakover voltage versus junction temperature.

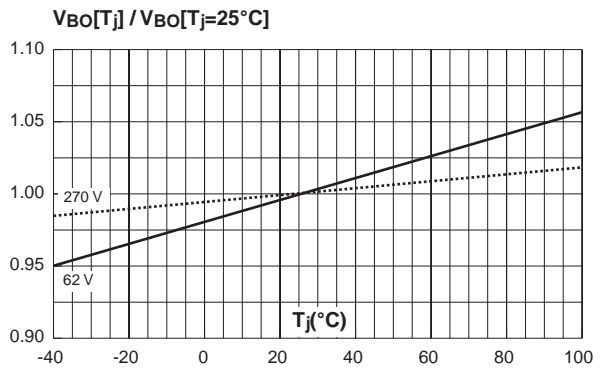


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).

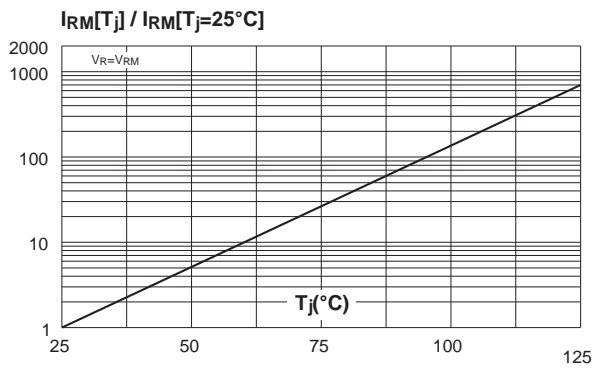


Fig. 6: Relative variation of thermal impedance versus pulse duration.

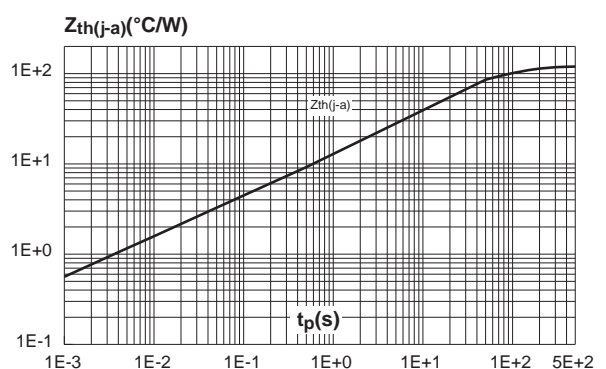
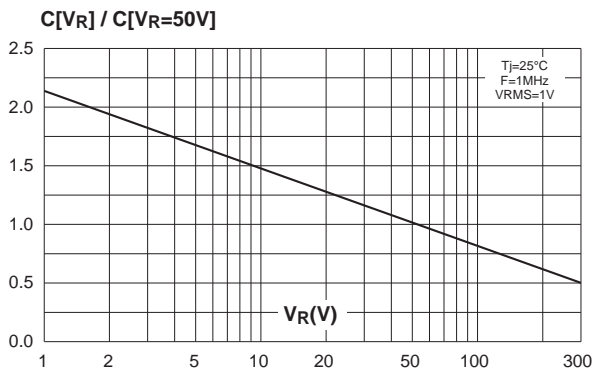
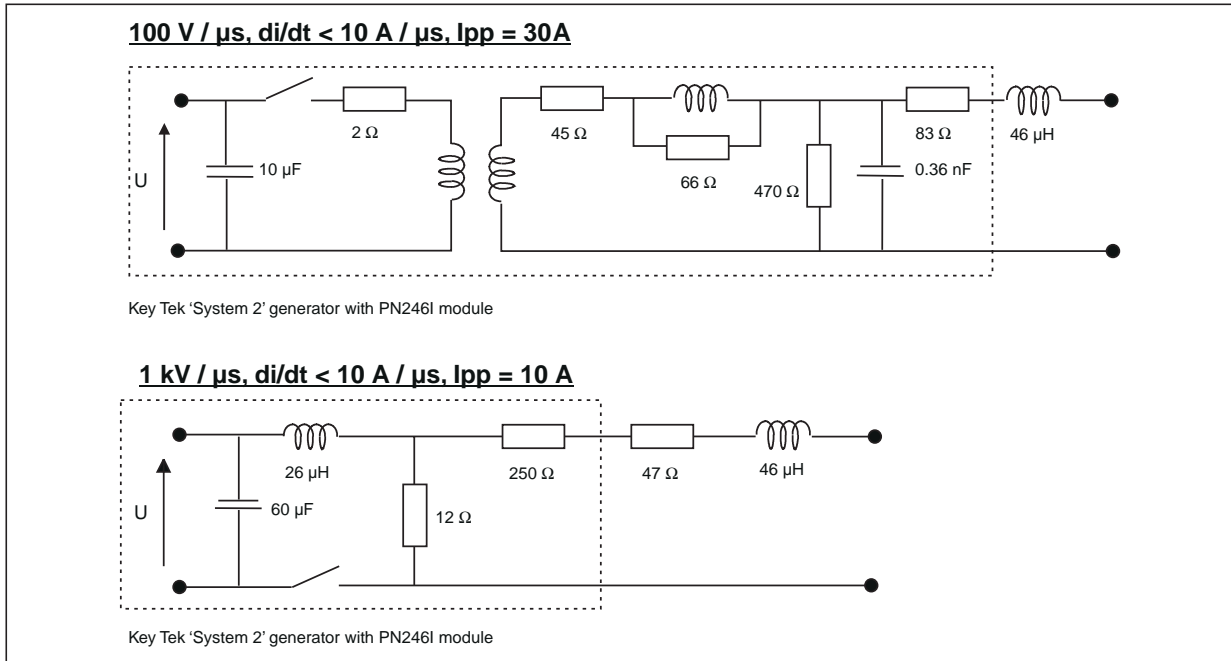


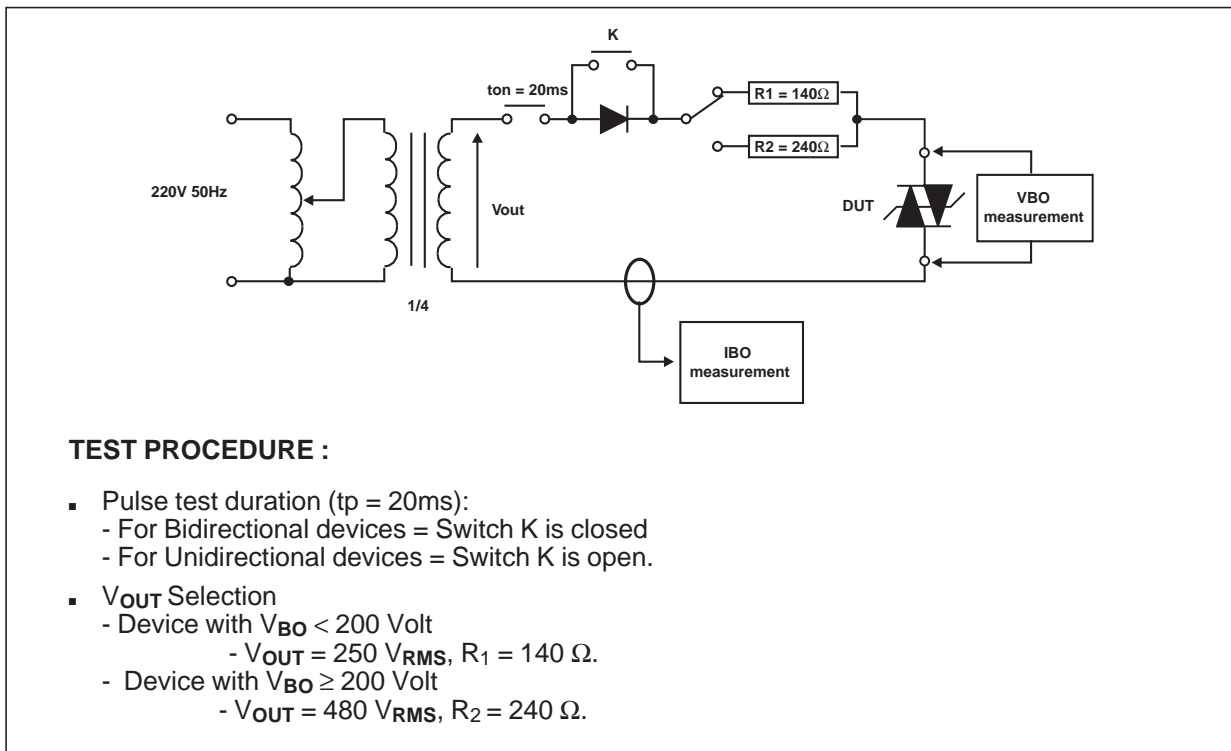
Fig. 7: Relative variation of junction capacitance versus reverse voltage applied (typical values).



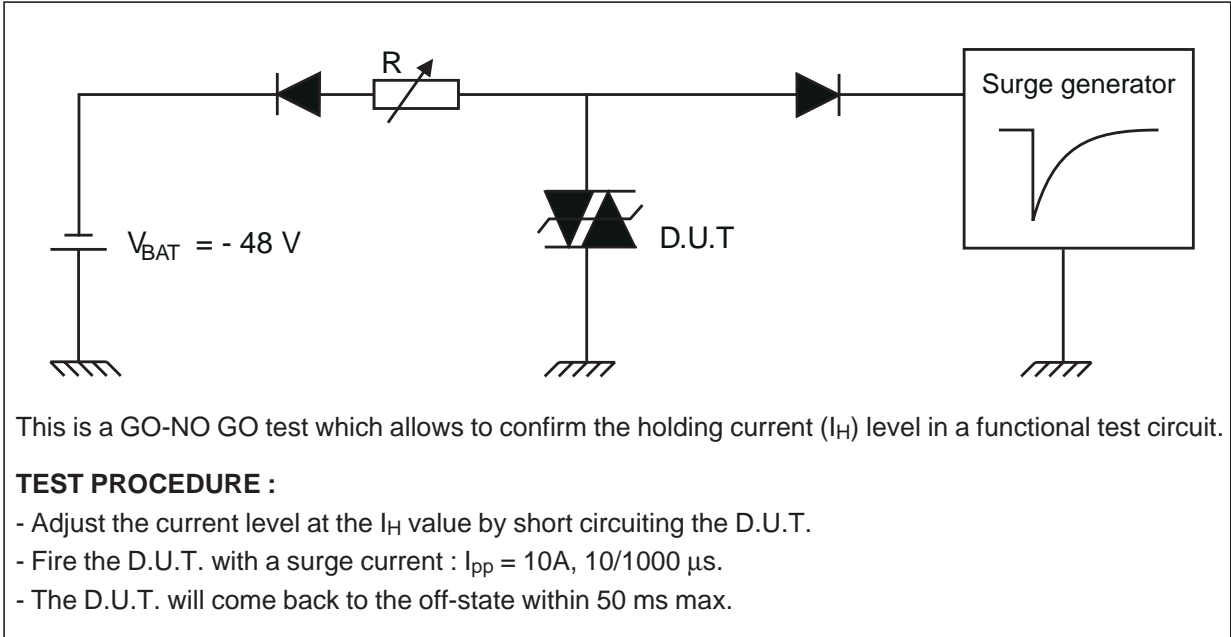
TEST CIRCUIT 1 FOR DYNAMIC I_{BO} and V_{BO} PARAMETERS



TEST CIRCUIT 2 for I_{BO} AND V_{BO} PARAMETERS.



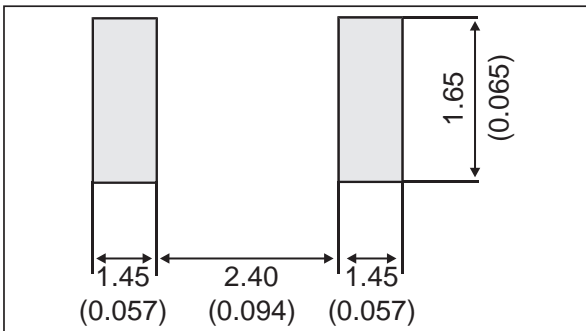
TEST CIRCUIT 3 for I_H PARAMETERS.



PACKAGE MECHANICAL DATA
SMA (JEDEC DO-214AC)

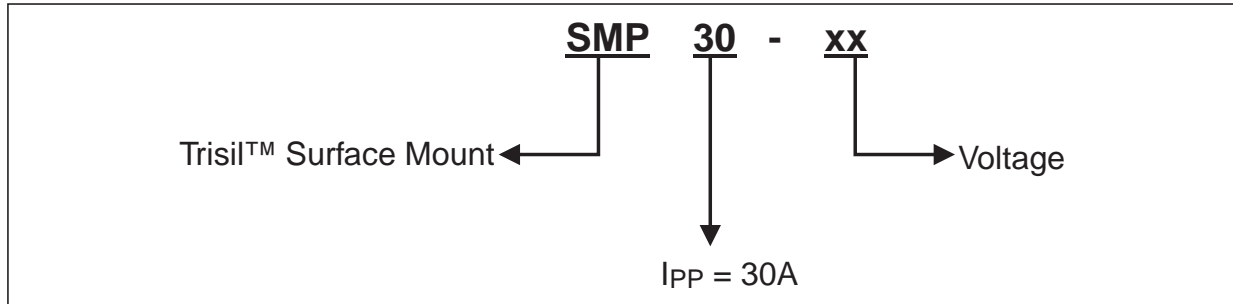
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.70	0.075	0.106
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.41	0.006	0.016
E	4.80	5.60	0.189	0.220
E1	3.95	4.60	0.156	0.181
D	2.25	2.95	0.089	0.116
L	0.75	1.60	0.030	0.063

FOOT PRINT in millimeters (in inches)



SMP30-xxx

ORDER CODE



ORDERING INFORMATION

Part number	Marking	Package	Weight	Base qty	Delivery mode
SMP30-62	QA4	SMA	0.06 g	5000	Tape & reel
SMP30-68	QAB				
SMP30-100	QAC				
SMP30-120	QAD				
SMP30-130	QAE				
SMP30-180	QAF				
SMP30-200	QAG				
SMP30-220	QAH				
SMP30-240	QAI				
SMP30-270	QAJ				

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